

2MBI1000VXB-170E-54

IGBT Modules

IGBT MODULE (V series) 1700V / 1000A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines


■ Maximum Ratings and Characteristics
● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units
Collector-Emitter voltage	V _{CES}		1700	V
Gate-Emitter voltage	V _{GES}		±20	V
Inverter Collector current	I _c	Continuous	T _c =25°C 1400	A
	I _{c pulse}	1ms	2000	
	-I _c		1000	
	-I _{c pulse}	1ms	2000	
Collector power dissipation	P _C	1 device	6250	W
Junction temperature	T _j		175	°C
Operating junction temperature (under switching conditions)	T _{jop}		150	
Case temperature	T _c		150	
Storage temperature	T _{stg}		-40 ~ +150	
Isolation voltage	V _{iso}	AC : 1min.	4000	VAC
Screw torque (*3)	-	Mounting	6.0	N m
		Main Terminals	10.0	
		Sense Terminals	2.1	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value : Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value : Main Terminals 8.0 ~ 10.0 Nm (M8)
Recommendable Value : Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at T_j = 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
Inverter	Zero gate voltage collector current	I _{CES}	V _{GE} = 0V, V _{CE} = 1700V	-	-	6.0	mA	
	Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	1200	nA	
	Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 1000mA	6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V _{CE(sat)} (terminal) (*4)	V _{GE} = 15V I _c = 1000A	T _j = 25°C	-	2.10	2.55	V
				T _j = 125°C	-	2.50	-	
				T _j = 150°C	-	2.55	-	
		V _{CE(sat)} (chip)		T _j = 25°C	-	2.00	2.45	
				T _j = 125°C	-	2.40	-	
	Input capacitance	R _{g(int)}	-	-	1.17	-	Ω	
		C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	94	-	nF	
	Turn-on time	t _{on}	V _{CC} = 900V I _c = 1000A	-	1250	-	nsec	
		t _{r(l)}	V _{GE} = ±15V	-	500	-		
	Turn-off time	t _{off}	R _G = +1.2/-1.8Ω	-	1550	-	nsec	
		t _r	L _S = 60nH	-	150	-		
	Forward on voltage	V _F (terminal) (*4)	V _{GE} = 0V I _F = 1000A	T _j = 25°C	-	1.95	2.40	V
T _j = 125°C				-	2.20	-		
T _j = 150°C				-	2.15	-		
V _F (chip)		T _j = 25°C		-	1.85	2.30		
		T _j = 125°C		-	2.10	-		
Reverse recovery time	t _{rr}	I _F = 1000A	-	240	-	nsec		
	Resistance	R	T = 25°C	-	5000	-	Ω	
T = 100°C			465	495	520			
Thermistor	B value	B	T = 25/50°C	3305	3375	3450	K	

Note *1: Please refer to page 7, there is definition of on-state voltage at terminal.

● Thermal resistance characteristics

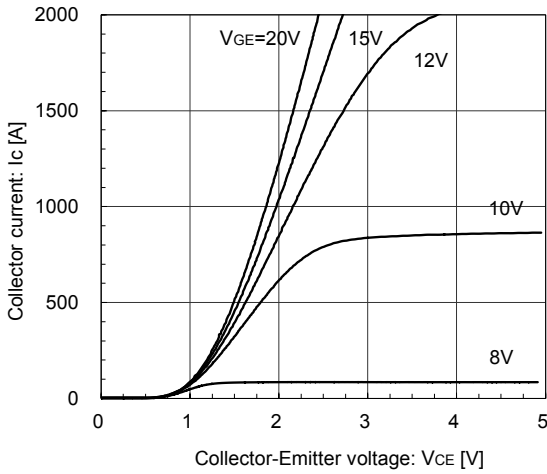
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	Inverter IGBT Inverter FWD	-	-	0.024	°C/W
Contact thermal resistance (1device) (*5)	R _{th(c-f)}	with Thermal Compound	-	0.0083	-	

Note *5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

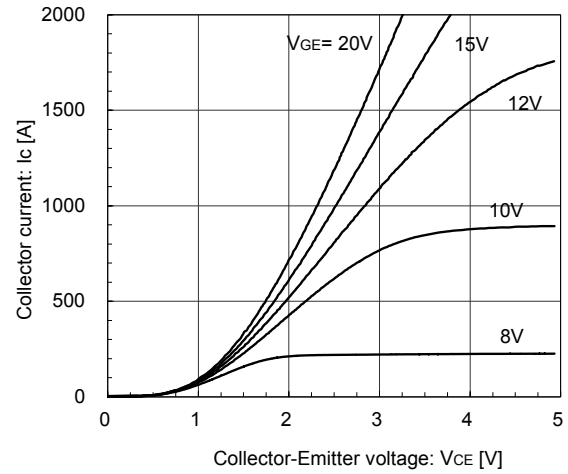
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
T_j = 25°C / chip



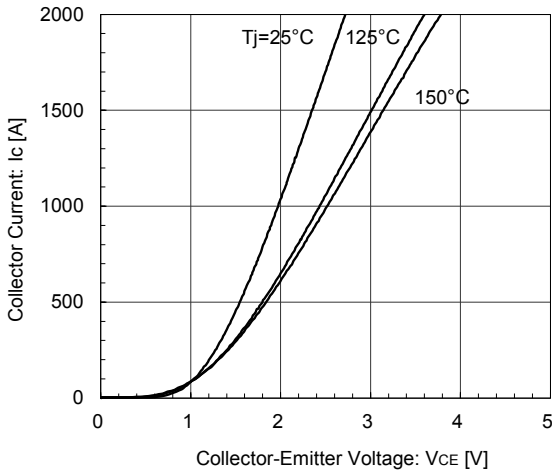
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
T_j = 150°C / chip



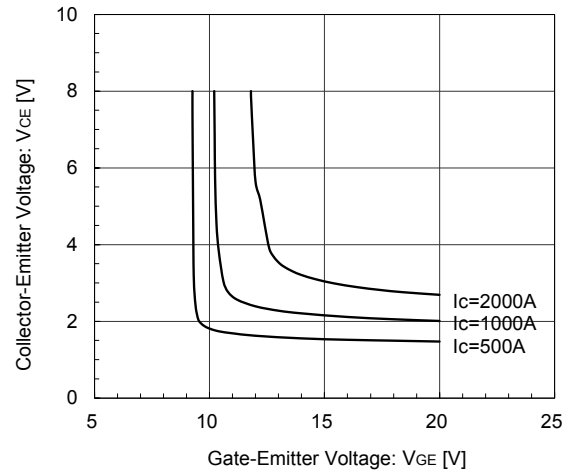
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
V_{GE} = 15V / chip



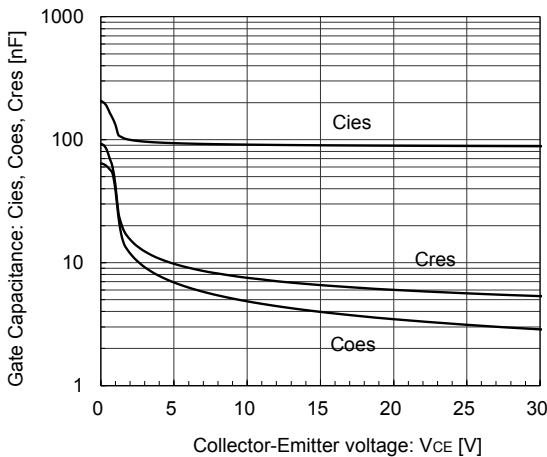
[INVERTER]

Collector-Emittter voltage vs. Gate-Emittter voltage (typ.)
T_j = 25°C / chip



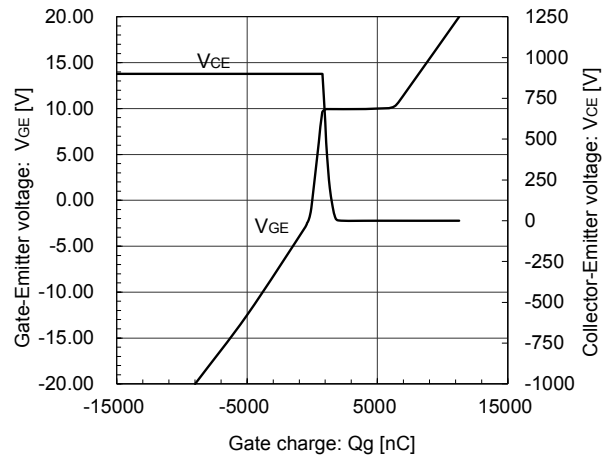
[INVERTER]

Gate Capacitance vs. Collector-Emittter Voltage (typ.)
V_{GE} = 0V, f = 1MHz, T_j = 25°C



[INVERTER]

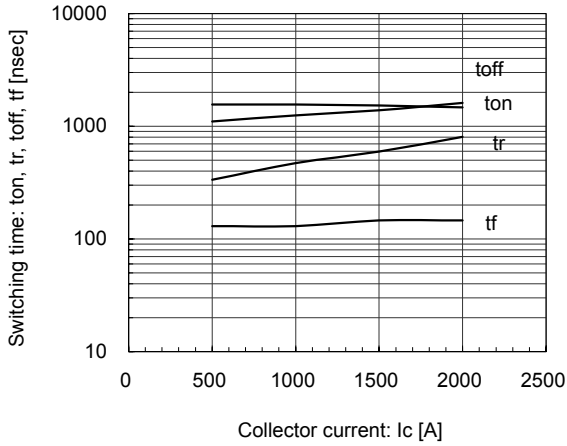
Dynamic Gate Charge (typ.)
V_{CC} = 900V, I_c = 1000A, T_j = 25°C



[INVERTER]

Switching time vs. Collector current (typ.)

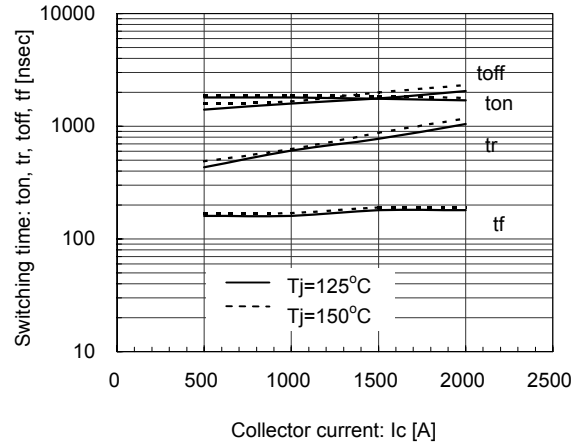
V_{CC}=900V, V_{GE}=±15V, R_G=+1.2/-1.8Ω, T_J=25°C



[INVERTER]

Switching time vs. Collector current (typ.)

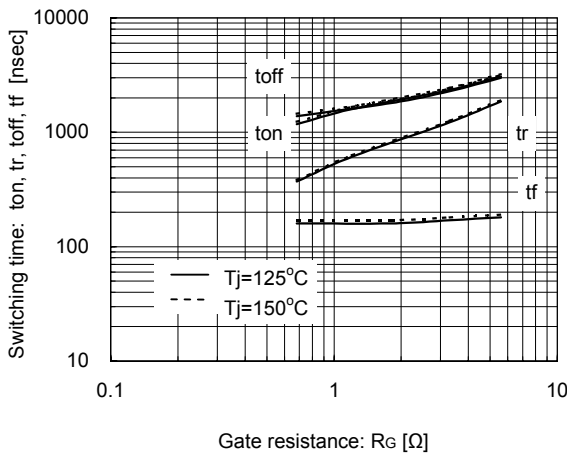
V_{CC}=900V, V_{GE}=±15V, R_G=+1.2/-1.8Ω, T_J=125°C, 150°C



[INVERTER]

Switching time vs. Gate resistance (typ.)

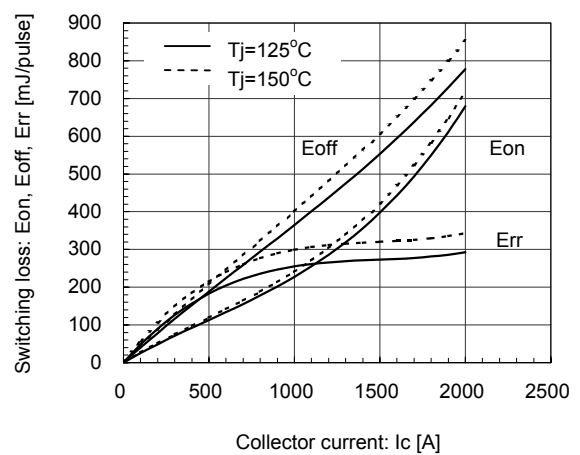
V_{CC}=900V, I_C=1000A, V_{GE}=±15V, T_J=125°C, 150°C



[INVERTER]

Switching loss vs. Collector current (typ.)

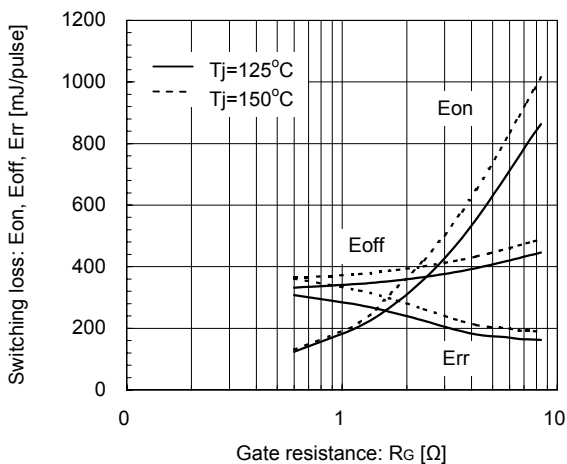
V_{CC}=900V, V_{GE}=±15V, R_G=+1.2/-1.8Ω, T_J=125°C, 150°C



[INVERTER]

Switching loss vs. Gate resistance (typ.)

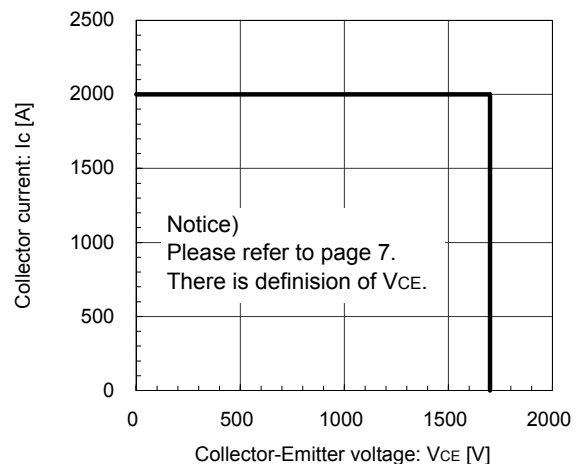
V_{CC}=900V, I_C=1000A, V_{GE}=±15V, T_J=125°C, 150°C

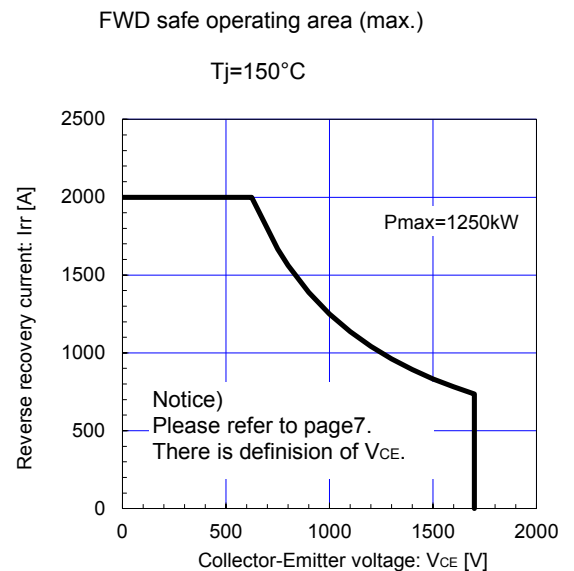
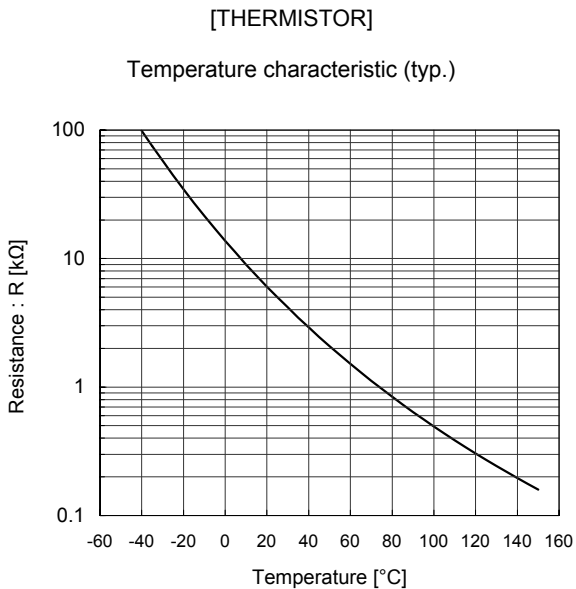
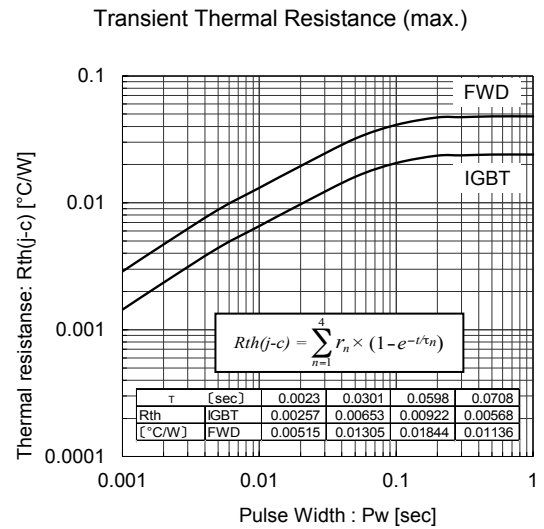
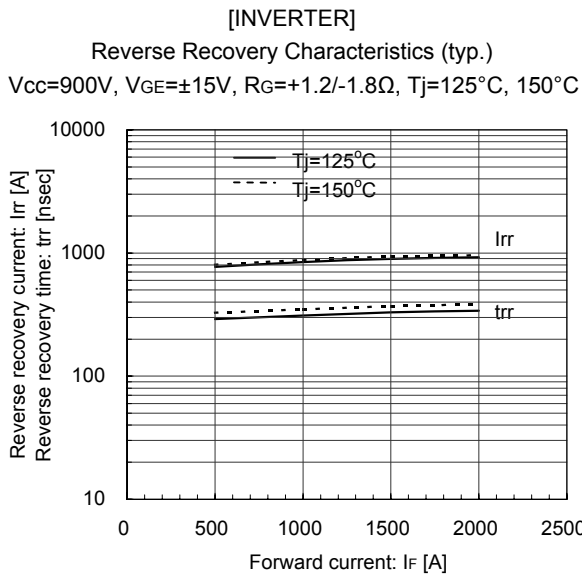
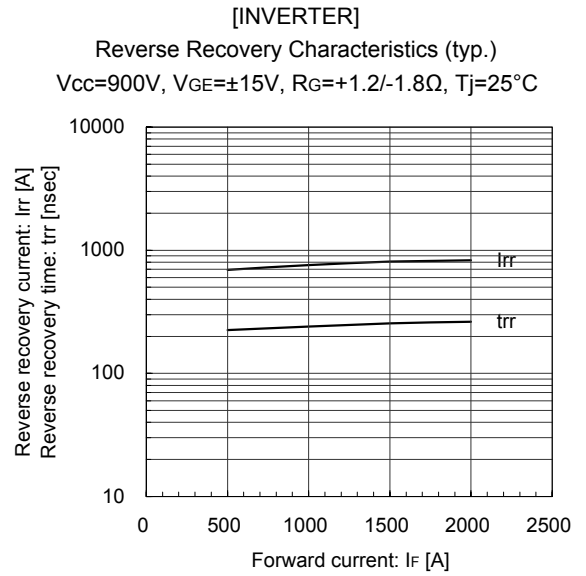
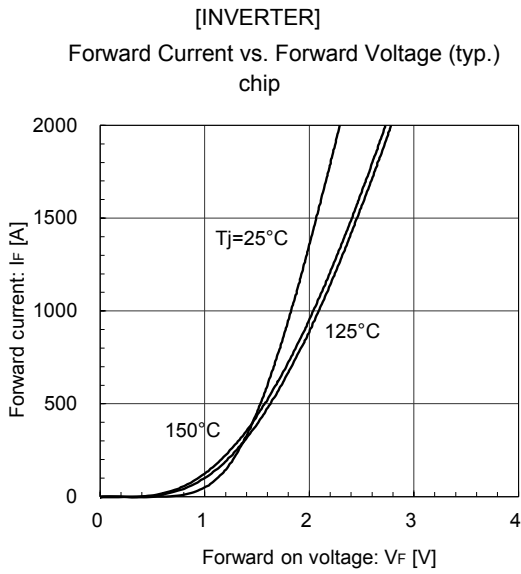


[INVERTER]

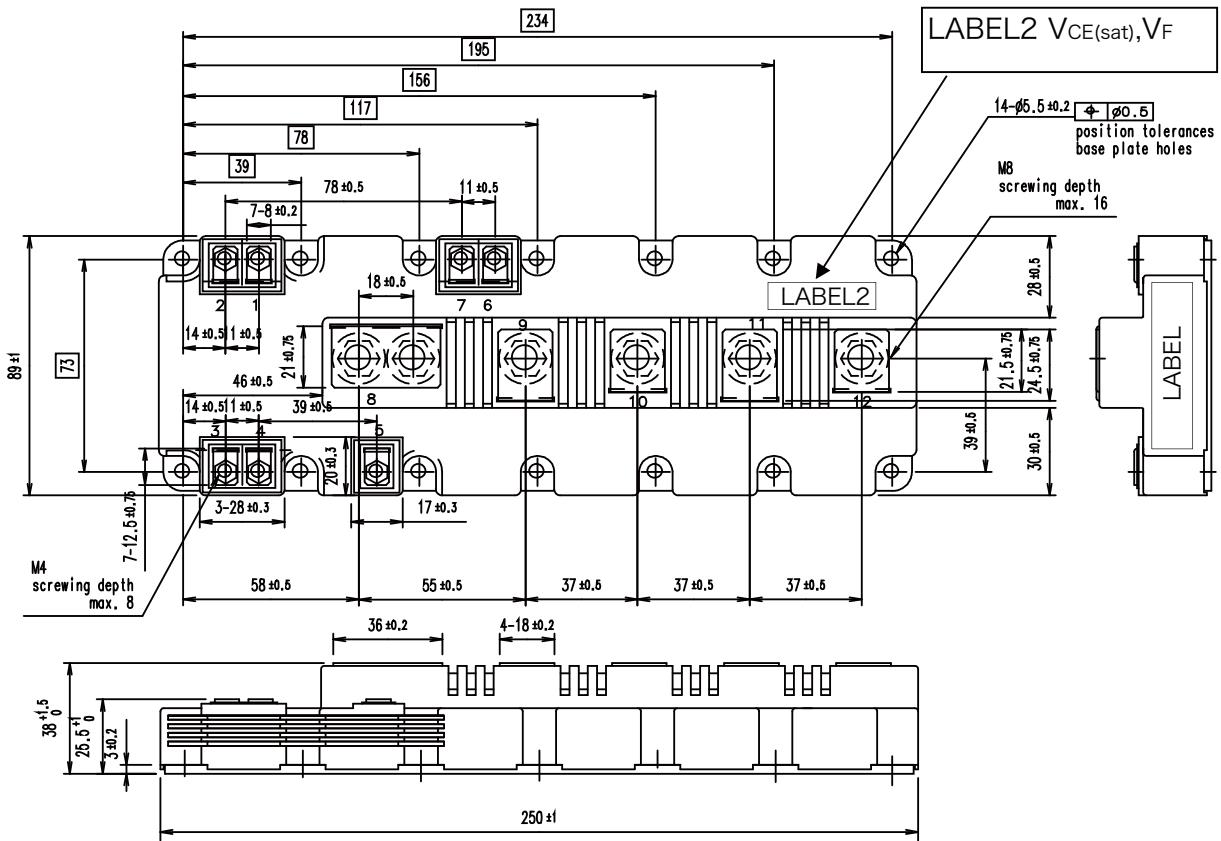
Reverse bias safe operating area (max.)

+V_{GE}=15V, -V_{GE}=15V, R_G=+1.2/-1.8Ω, T_J=150°C



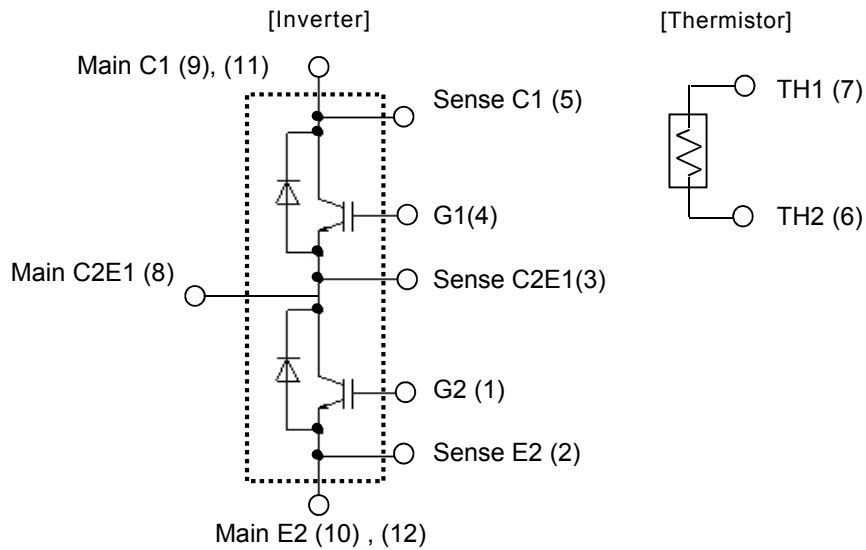


■ Outline Drawings, mm

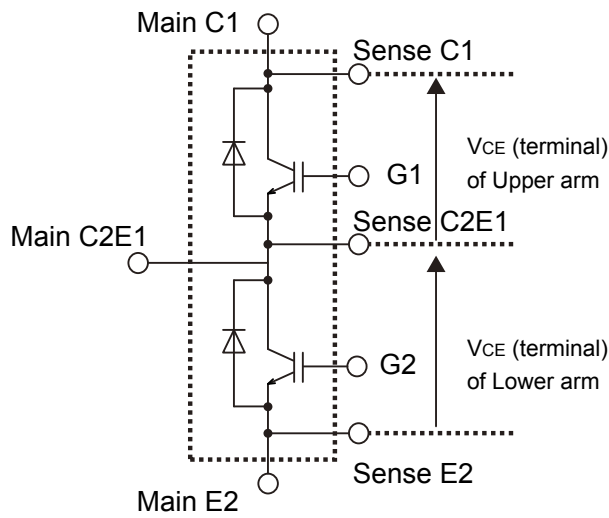


Weight: 1250g(typ.)

■ Equivalent Circuit Schematic



■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined V_{CE} value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Switching characteristics of V_{CE} also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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